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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/759,444	01/14/2004	Chi tse Wu	H0002800US(4015)	7831
128 7590 07/14/2009 HONEYWELL INTERNATIONAL INC.			EXAMINER	
PATENT SERVICES			MCDONALD, RODNEY GLENN	
101 COLUMBIA ROAD P O BOX 2245		ART UNIT	PAPER NUMBER	
MORRISTOWN, NJ 07962-2245			1795	
			MAIL DATE	DELIVERY MODE
			07/14/2009	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)				
	10/759,444	WU ET AL.				
Office Action Summary	Examiner	Art Unit				
,						
The MAILING DATE of this communication ann	Rodney G. McDonald	1795				
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply						
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.  - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.  - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).						
Status						
1) Responsive to communication(s) filed on <u>01 Ju</u>	dv 2009					
	action is non-final.					
·=	/ <del></del>					
closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims						
4)⊠ Claim(s) <u>67-76</u> is/are pending in the application.						
4a) Of the above claim(s) is/are withdrawn from consideration.						
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>67-76</u> is/are rejected.						
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/or	8) Claim(s) are subject to restriction and/or election requirement.					
Application Papers						
9) The specification is objected to by the Examine	r.					
10) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).						
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of:						
1. Certified copies of the priority documents have been received.						
2. Certified copies of the priority documents have been received in Application No						
3. Copies of the certified copies of the priority documents have been received in this National Stage						
application from the International Bureau (PCT Rule 17.2(a)).						
* See the attached detailed Office action for a list of the certified copies not received.						
Attachment(s)						
Attachment(s)  1) Notice of References Cited (PTO-892)  4) Interview Summary (PTO-413)						
2) Notice of Draftsperson's Patent Drawing Review (PTO-948) Paper No(s)/Mail Date						
3) Information Disclosure Statement(s) (PTO/SB/08)  Paper No(s)/Mail Date  5) Motice of Informal Patent Application 6) Other:						
1 apot 110(a),miaii Date						

## **DETAILED ACTION**

## Continued Examination Under 37 CFR 1.114

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on July 1, 2009 has been entered.

## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

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Claims 67, 70 and 72-76 are rejected under 35 U.S.C. 103(a) as being unpatentable over Fai Lai (U.S. Pat. 6,217,716) in view of Kardokus et al. (U.S. Pat. 6,113,761).

Regarding claim 67, Fai Lai teaches a three dimensional physical vapor deposition target. The target can comprise a material for metallization such as Al or Ti. The target has a shape, the shape includes at least one cup having a first end and a second end in opposing relation to the first end. The first end having an opening extending therein. The cup having a hollow therein. The hollow extending from the opening in the first end toward the second end. The cup having an interior surface defining a periphery of the hollow. A sputtering surface defined along the interior surface of the cup. The target is monolithic. (Column 2 lines 14-18; Column 6 lines 65-68; Column 7 lines 1-31; Figs. 6-10, 12, 13) As to the target comprising a cast ingot the process is given no weight since the product is substantially identical to the claimed subject matter. It should be noted that [E]ven though product-by-process claims are limited by and defined by the process, determination of patentability is based on the product itself. The patentability of a product does not depend on its method of production. If the product in the product-by-process claim is the same as or obvious from a product of the prior art, the claim is unpatentable even though the prior product was made by a different process." In re Thorpe, 777F.2d 695, 698, 227 USPQ 964, 966 (Fed. Cir. 1985) (citations omitted)

The differences between Fai Lai and the present claims is that the average grain size of less than or equal to 250 microns is not discussed (claim 67), the target being

CuSn with Sn being present from about 100 ppm to about 3 atomic percent (Claim 70), the target being CuAg with Ag being present from about 100 ppm to about 3 atomic percent (Claim 72) and the grain size of the target is not discussed (Claims 73-76).

Regarding claim 67, 73-76, Kardokus et al. teach the grain size of a target to be not more than 50 microns. (Column 8 lines 57-59)

Regarding claim 70, Kardokus et al. teach Sn present with CuSn. Alloying levels typically can be at least about 100 ppm. (Column 5 lines 8-16; Column 5 lines 20-24)

Regarding claim 72, Kardokus et al. teach Ag present with CuAg. Alloying levels typically can be at least about 100 ppm. (Column 5 lines 8-16; Column 5 lines 20-24)

The motivation for utilizing the features of Kardokus et al. is that it allows for forming interconnects on wafers. (Column 2 lines 43-45)

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to have modified Fai Lai by utilizing the features of Kardokus et al. because it allows for forming interconnects on wafers.

Claim 68 is rejected under 35 U.S.C. 103(a) as being unpatentable over Fai Lai in view of Kardokus et al. as applied to claims 67, 70 and 72-76 above, and further in view of Kulkarni et al. (U.S. Pat. 6,283,357).

The difference not yet discussed is the target material consisting essentially of copper and wherein the target consists essentially of the same material. (Claim 68).

Regarding claim 68, Kulkarni et al. suggest various materials for sputtering targets. Among those materials is suggested copper. (Column 3 lines 35-51)

The motivation for utilizing a copper target is that it allows forming copper interconnects for metallization. (Column 3 lines 35-51)

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to have utilized the features of Kulkarni because it allows for forming copper interconnects for metallization.

Claim 69 is rejected under 35 U.S.C. 103(a) as being unpatentable over Fai Lai in view of Kardokus et al. as applied to claims 67, 70 and 72-76 above, and further in view of Michaluk (WO 00/31310).

The difference not yet discussed is the target being made of tantalum with specific grain size is not discussed (claim 69).

Regarding claim 69, Michaluk et al. teach the grain size of a tantalum target to be not more than 50 microns. (See Abstract)

The motivation for utilizing the features of Michaluk et al. is that it allows for forming uniform films. (See Page 1 lines 27-28

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to have utilized the features of Michaluk et al. because it allows for forming uniform films.

Claim 71 is rejected under 35 U.S.C. 103(a) as being unpatentable over Fai Lai in view of Kardokus et al. as applied to claims 67, 70 and 72-76 above, and further in view of Pavate et al. (U.S. Pat. 6,391,163).

The difference not yet discussed is utilizing aluminum in the copper target.

(Claim 71)

Regarding claim 71, Pavate et al. teach utilizing aluminum ion a copper target. (Column 3 lines 20-29)

The motivation for utilizing the features of Pavate et al. is that it allows for increasing the hardness of the target. (Column 3 lines 20-29)

Therefore, it would have been obvious to one of ordinary skill in the art at the invention was made to have utilized the features of Pavate et al. because it allows for increasing the hardness of the target.

## REMARKS:

In response to the argument that the prior art does not teach mnonolithic targets, it is argued that Fai Lai teaches a target that is monolithic as there is no backing plate attached thereto. (See Figs. 6-10, 12, 13)

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Rodney G. McDonald whose telephone number is 571-272-1340. The examiner can normally be reached on M-Th with every Friday off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nam X. Nguyen can be reached on 571-272-1342. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Rodney G. McDonald/ Primary Examiner, Art Unit 1795

Rodney G. McDonald Primary Examiner Art Unit 1795

RM July 14, 2009